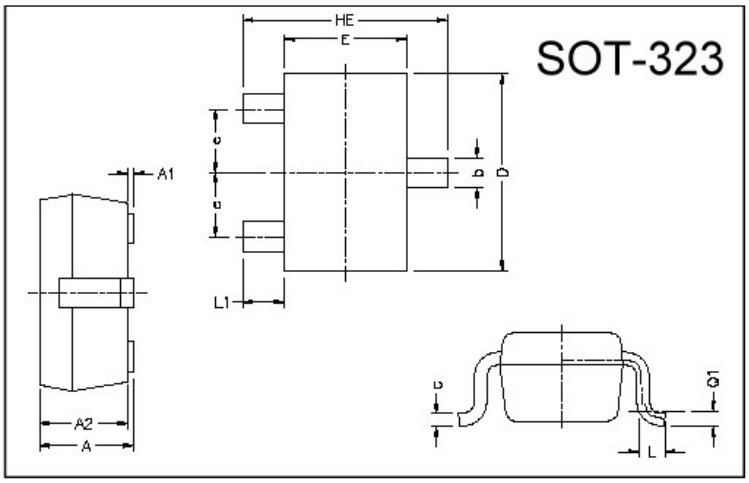
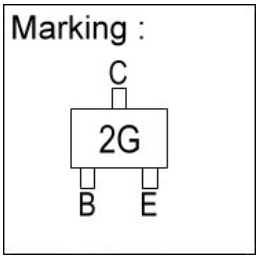
GSMBTA56 PNP SILICON TRANSISTOR

Description

The GSMBTA56 is designed for general purpose amplifier applications.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

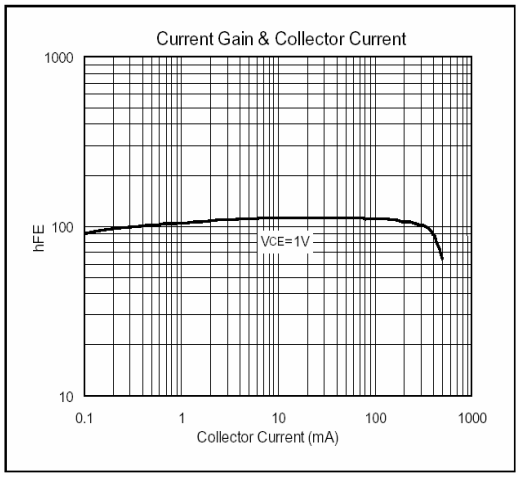
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-4	V
Collector Current	I_C	-500	mA
Total Power Dissipation	P_D	225	mW

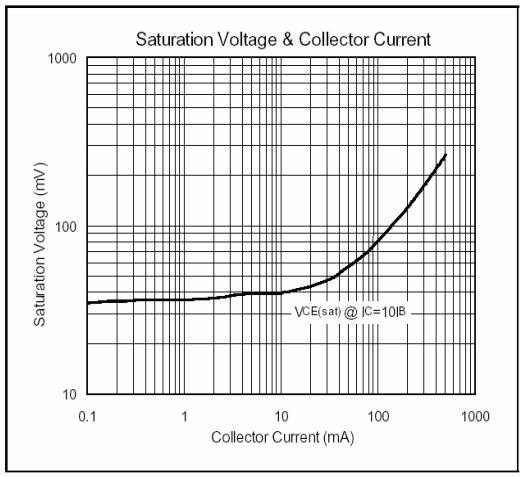
Electrical Characteristics(Ta = 25℃,unless otherwise noted)

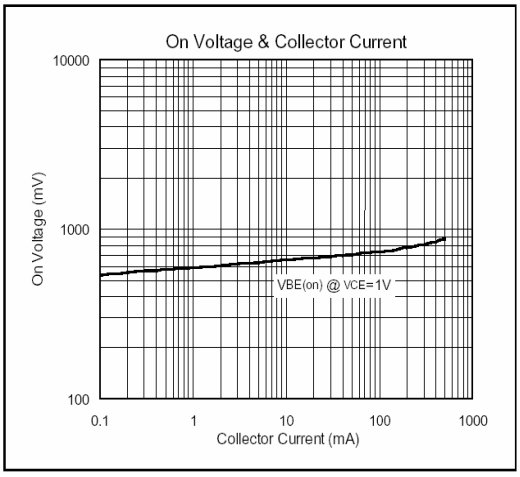
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-80	-	-	V	I_C=-100uA, I_E=0
BV_{CEO}	-80	-	-	V	I_C=-1mA, I_B=0
BV_{EBO}	-4	-	-	V	I_E=-100uA, I_C=0
I_{CBO}	-	-	-100	nA	V_{CB}=-80V, I_E=0
I_{CEO}	-	-	-100	nA	V_{CE}=-60V, I_B=0
*$V_{CE(sat)}$	-	-	-250	mV	I_C=-100mA, I_B=-10mA
*$V_{BE(on)}$	-	-	-1.2	V	V_{CE}=-1V, I_C=-100mA
*h_{FE}1	50	-	-		V_{CE}=-1V, I_C=-10mA
*h_{FE}2	50	-	-		V_{CE}=-1V, I_C=-100mA
fT	100	-	-	MHz	V_{CE}=-2V, I_C=-10mA, f=100MHz

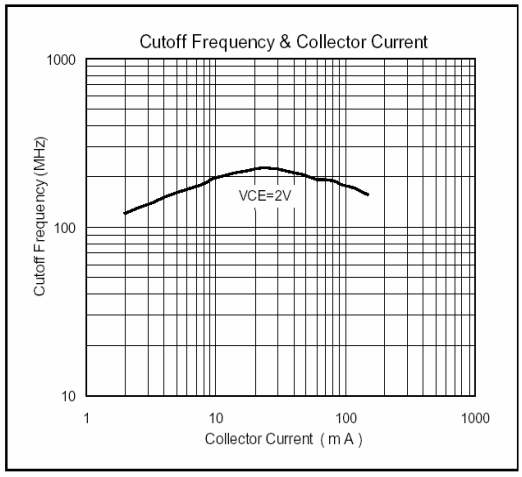
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

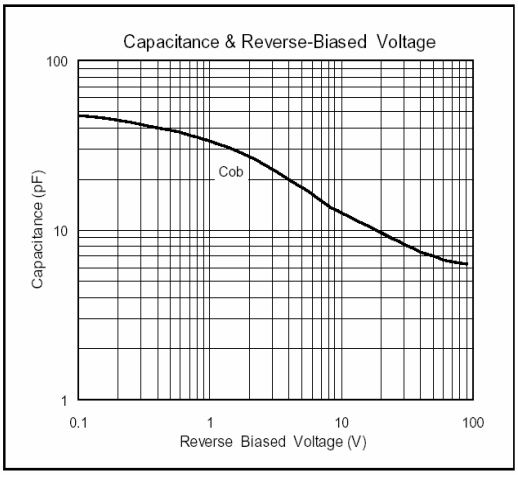
Characteristics Curve

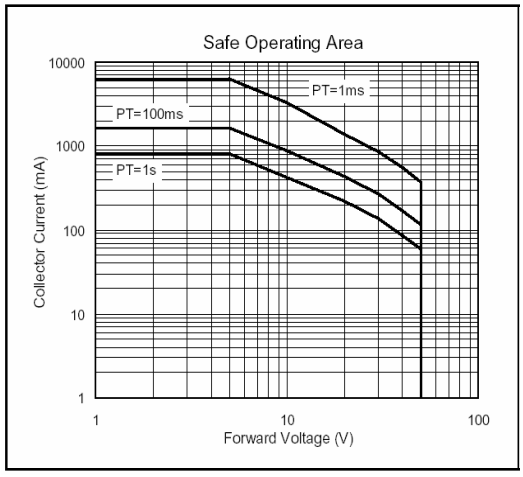












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